

PHOTOLITHOGRAPHY FACILITY



MODEL: MA6/BA6 SUSS MICROTECH

INSTALLATION PLACE: Cleanroom of “Nanotechnology and Microsystems Laboratory”, Department of Microelectronics

DESCRIPTION: Mask Aligner for High Resolution Lithography with SUSS Split-field Microscope M204. Photoresist is spin-coated using Karl-Suss RC8 tool and is baked using high-precision hot-plate by ATV.

SPECIFICATIONS

1. Exposure UV: Broad band 250nm-450nm, 365nm
2. Sample size: 75mm and 100mm
3. Exposure programs: Vacuum contact, soft contact, hard contact
4. X-Y shift: below 0.1 μ m
5. Resolution: 0.6 μ m in vacuum contact
6. Double side alignment facility

APPLICATIONS

1. Photoresist Patterning for Microelectronics devices and ICs
2. MEMS
3. Generic substrate patterning
4. Photoresist studies

CERTIFICATION/ACCREDITATION

The facility is ISO 9001:2008 certified for 0.8 μ m, 1 μ m and 2 μ m line widths

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